

What is claimed is:

1. A method for fabricating a device comprising the steps of:
  - forming a substrate;
  - forming a contact plug through said substrate;
  - forming a first electrode on said substrate;
  - forming a dielectric layer on said first electrode;
  - forming a second electrode on said dielectric layer;
  - applying an interlayer dielectric layer to said second electrode and exposed surfaces of said first electrode and/or said dielectric layer;
  - applying chemical mechanical polishing to said interlayer dielectric layer to expose a surface of said second electrode;
  - depositing a metal layer on said interlayer dielectric layer and said exposed surface of said second electrode;
  - etching said metal layer to provide an interconnection pattern to said second electrode.
2. The method according to claim 1, further comprising forming a first layer on said substrate, the step of forming said first electrode comprising forming said first electrode on said first layer.
3. The method of claim 1, wherein the step of forming a first electrode comprises connecting said first electrode to said plug through said first layer.
4. The method of claim 1, wherein said exposed surface of said second electrode has a first surface area, and said metal layer has a surface having a second surface area, said surface of said metal layer contacting said exposed

second electrode, and wherein the step of etching said metal layer comprises etching said metal layer such that said second surface area is greater than said first surface area.

5. The method of claim 4, wherein said first electrode has a surface area, and the step of etching said metal layer comprises etching said metal layer such that said surface area of said metal layer is substantially equal to said surface area of said first electrode.

6. The method of claim 1, wherein the step of forming a dielectric layer on said first electrode comprises forming a ferroelectric layer on said first electrode.

7. A device comprising:

a substrate having a contact plug extending therethrough;

a capacitor having a dielectric layer between a first electrode and a second electrode, said capacitor being mountable on said substrate;

said first electrode being formed on said substrate; and

said second electrode directly contacting an interdevice connecting metal pattern.

8. A device according to claim 7 wherein said first electrode is formed on an insulating layer formed on said substrate.

9. A device according to claim 8, wherein said insulating layer is an electrically insulating layer.

10. A device according to claim 7, wherein said first electrode and said contact plug are electrically connected.

11. A device according to claim 7, wherein said dielectric layer comprises a ferroelectric layer.
12. The device of claim 7, wherein said interdevice connecting metal pattern is formed of a metal layer applied to said capacitor.
13. The device of claim 7, wherein said interdevice connecting metal pattern is etched.
14. The device of claim 12, wherein said second electrode has a first surface area contacting said interdevice connecting metal pattern, and said metal layer has a surface having a second surface area, said surface of said metal layer contacting said second electrode, and wherein said second surface area is greater than said first surface area.
15. The device of claim 12, wherein said first electrode has a surface area, and said metal layer has a surface having a second surface area, said surface of said metal layer contacting said second electrode, said surface area of said metal layer being substantially equal to said surface area of said first electrode.